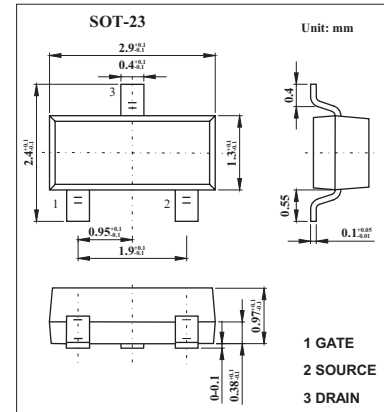
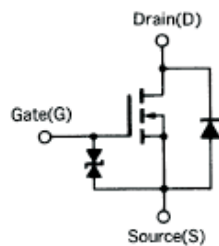


MOS Field Effect Transistor

2SK1133

■ Features

- Directly driven by Ics having a 5V power source.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the biasresistor.



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Rating | Unit |
|-------------------------|------------------|-------------|------|
| Drain to source voltage | V _{DSS} | 50 | V |
| Gate to source voltage | V _{GSS} | ±7.0 | V |
| Drain current (DC) | I _D | ±100 | m A |
| Drain current(pulse) * | I _D | ±200 | mA |
| Power dissipation | P _D | 200 | m W |
| Channel temperature | T _{ch} | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |

* PW ≤ 10ms, duty cycle ≤ 50%

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|-------------------------------------|----------------------|---|-----|-----|-----|------|
| Drain cut-off current | I _{DSS} | V _{DS} =50V, V _{GS} =0 | | | -10 | μ A |
| Gate leakage current | I _{GSS} | V _{GS} =±7V, V _{DS} =0 | | | ±10 | μ A |
| Gate to source cutoff voltage | V _{GS(off)} | V _{DS} =5.0V, I _D =1 μ A | 1.0 | 1.7 | 2.0 | V |
| Forward transfer admittance | Y _{fs} | V _{DS} =5.0V, I _D =20mA | 20 | 40 | | ms |
| Drain to source on-state resistance | R _{DS(on)} | V _{GS} =4V, I _D =20mA | | 16 | 50 | Ω |
| Input capacitance | C _{iss} | V _{DS} =5.0V, V _{GS} =0, f=1MHz | | 7 | | pF |
| Output capacitance | C _{oss} | | | 6 | | pF |
| Reverse transfer capacitance | C _{rss} | | | 2 | | pF |
| Turn-on delay time | t _{d(on)} | V _{GS(on)} =0, V _{DD} =5V, f=1MHz | | 6 | | ns |
| Rise time | t _r | | | 25 | | ns |
| Turn-off delay time | t _{d(off)} | | | 36 | | ns |
| Fall time | t _f | | | 35 | | ns |

■ Marking

| | |
|---------|-----|
| Marking | G11 |
|---------|-----|